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Team Nexperia

PDTC143EMB



NPN resistor-equipped transistor; R1 = 4.7 kΩ, R2 = 4.7 kΩ Rev. 1 — 7 June 2012 Product data sh

Product data sheet

1. **Product profile**

1.1 General description

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA143EMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs
- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Quick reference data Table 1.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)	1	3
3	3 O	output (collector)	2 Transparent	1 R1
			top view SOT883B (DFN1006B-3)	2 sym007

3. Ordering information

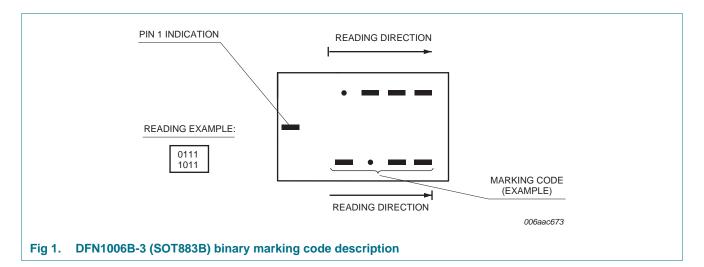
Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PDTC143EMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B	

4. Marking

Table 4. Marking codes

•	
Type number	Marking code
PDTC143EMB	0011 1010



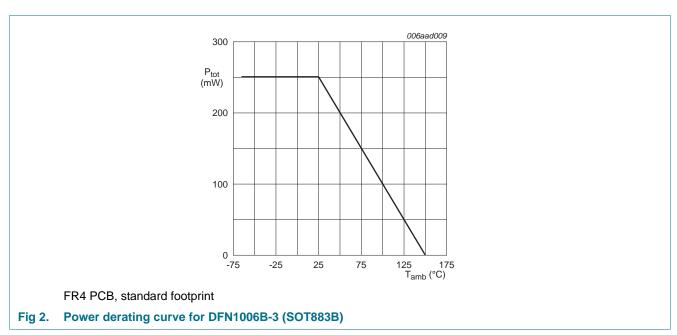
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	50	V
V_{CEO}	collector-emitter voltage	open base		-	50	V
V_{EBO}	emitter-base voltage	open collector		-	10	V
VI	input voltage	positive		-	30	V
		negative		-	-10	V
I _O	output current			-	100	mA
I _{CM}	peak collector current	pulsed; $t_p \le 1$ ms		-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

Table 6. Thermal characteristics

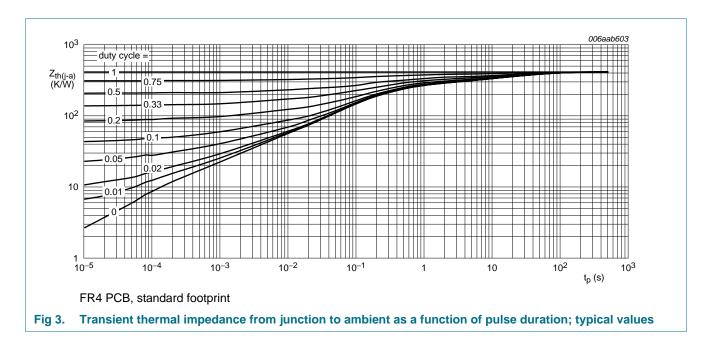
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	Ш	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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PDTC143EMB

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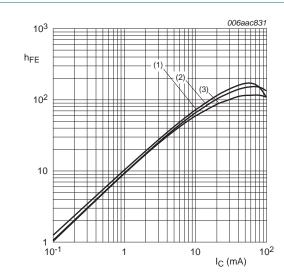


7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	1	μΑ
	current	$V_{CE} = 30 \text{ V}; I_B = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	900	μΑ
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 10 mA; T_{amb} = 25 °C		30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
V _{I(off)}	off-state input voltage	V_{CE} = 5 V; I_{C} = 100 μ A; T_{amb} = 25 °C		-	1.1	0.5	V
V _{I(on)}	on-state input voltage	V_{CE} = 0.3 V; I_{C} = 20 mA; T_{amb} = 25 °C		2.5	1.9	-	V
R1	bias resistor 1 (input)	T _{amb} = 25 °C		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio			0.8	1	1.2	
C _C	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	2.5	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	[1]	-	230	-	MHz

^[1] Characteristics of built-in transistor.



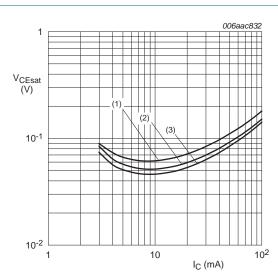
 $V_{CE} = 5 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



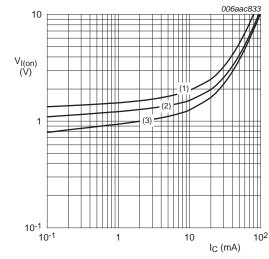
 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



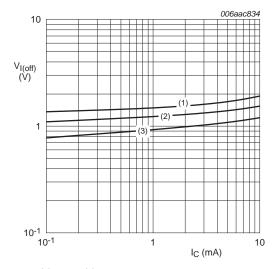
 $V_{CE} = 0.3 \text{ V}$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. On-state input voltage as a function of collector current; typical values



 $V_{CE} = 5 V$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Off-state input voltage as a function of collector current; typical values

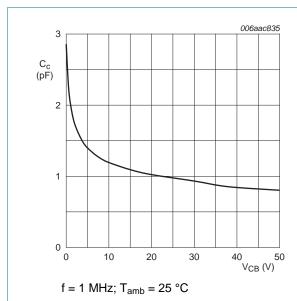


Fig 8. Collector capacitance as a function of collector-base voltage; typical values

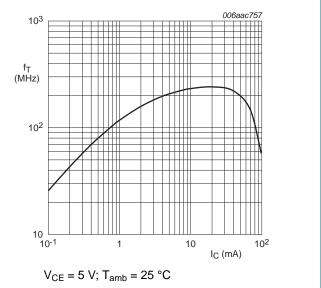


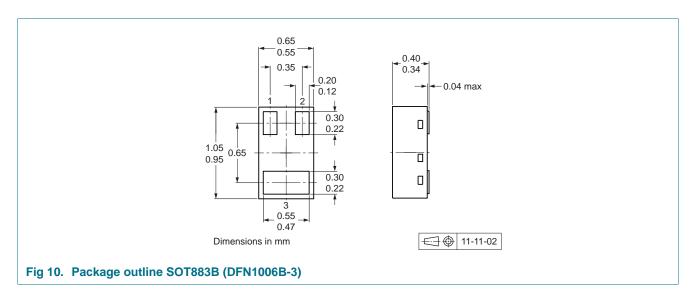
Fig 9. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

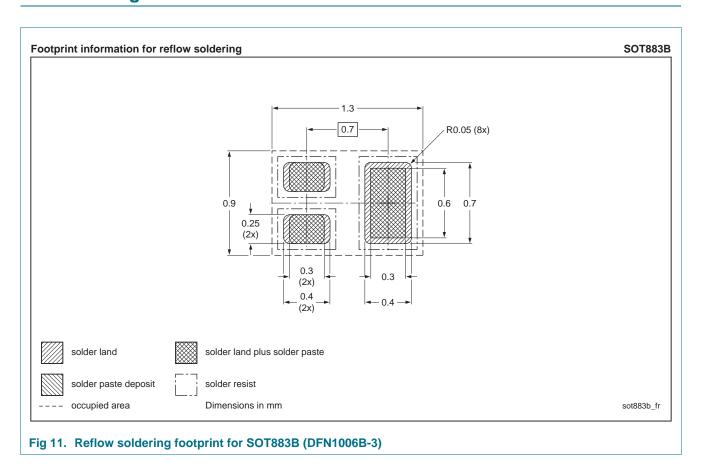
8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



10. Soldering





NPN resistor-equipped transistor; R1 = 4.7 kΩ, R2 = 4.7 kΩ

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC143EMB v.1	20120607	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTC143EMB

NPN resistor-equipped transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

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